	Application No.	Applicant(s)	Applicant(s)	
Notice of Allowability	09/755,572	ANG ET AL.		
	Examiner	Art Unit	1	
	Hsien-Ming Lee	2823	pr)	
The MAILING DATE of this communication appeall claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT Roof the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in or other appropriate communication is second communication.	n this application. If not inclu- unication will be mailed in du	ded e course. THIS	
1. This communication is responsive to <u>1/26/04</u> .				
2. ☑ The allowed claim(s) is/are <u>1-5 and 8-11</u> .				
3. The drawings filed on are accepted by the Examine	r.			
4. ☐ Acknowledgment is made of a claim for foreign priority uner a) ☐ All b) ☐ Some* c) ☐ None of the: 1. ☐ Certified copies of the priority documents have 2. ☐ Certified copies of the priority documents have 3. ☐ Copies of the certified copies of the priority documents have 3. ☐ Copies of the certified copies of the priority documents have 3. ☐ Copies of the certified copies of the priority documents have 3. ☐ Copies of the certified copies of the priority documents have 3. ☐ Copies of the certified copies of the priority documents have 3. ☐ Copies of the certified copies of the priority documents have 3. ☐ Copies of the priority documents have 3. ☐ Copies of the priority documents have 3. ☐ Certified copies not received: ☐ ☐ Certified Copies not received: ☐ ☐ ☐ ☐ ☐ ☐ ☐ ☐ ☐ ☐ ☐ ☐ ☐ ☐ ☐ ☐ ☐ ☐ ☐	e been received. e been received in Application comments have been received of this communication to file MENT of this application. Initted. Note the attached EX es reason(s) why the oath of the submitted. Is a Submitted of the submitted of t	on No In this national stage application this national stage application are a reply complying with the representation and the drawings in the front (not the transfer of the drawings in the front (not the transfer of the drawings in the submitted).	requirements NOTICE OF	
Attachment(s) 1. Notice of References Cited (PTO-892) 2. Notice of Draftperson's Patent Drawing Review (PTO-948) 3. Information Disclosure Statements (PTO-1449 or PTO/SB/Paper No./Mail Date	6. ☐ Interview S Paper No 08), 7. ☑ Examiner's 8. ☑ Examiner's 9. ☐ Other	Informal Patent Application (PSummary (PTO-413), Mail Date S Amendment/Comment S Statement of Reasons for A	Mowance	

Art Unit: 2823

DETAILED ACTION

Remarks

- 1. The rejection, as set forth in the previous Office Action, is withdrawn in response to applicant's arguments.
- 2. A <u>formal drawing</u> will be submitted by the applicant, as communicated with Rosemary L. S. Pike on April 13, 2004, in response to the examiner amendment as set forth in this Office Action, wherein a reference number "36" is added in <u>Figure 7</u>.
- 3. Claims 1-5 and 8-11 are pending in the application.

Examiner's Amendment

4. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview with Rosemary L. S. Pike (Reg. No. 39,332) on April 12, 2004.

5. The application has been amended as follows:

In claim 1, at line 16, replace "one said first trenches" with -- said first trench --; at line 25, replace "first contacts" with -- first contact openings --; and at lines 28-29, delete "in each of said active regions --.

In claim 8, at line 17, delete "one" after "wherein"; at line 26, replace "first contacts" with -- first contact openings --; and at lines 29-30, delete "in each of said active regions --.

In Figure 7, add a reference number "36" to refer to interlevel dielectric layer, as shown in marked-up Figure 7.

Art Unit: 2823

Allowable Subject Matter

6. Claims 1-5 and 8-11 are allowed.

7. The following is an examiner's statement of reasons for allowance:

The prior art of record, Babcock et al. (US 2002/0047155), teaches a method of forming a silicon-on-insulator device the fabrication of integrated circuits, comprising:

- providing a silicon layer 265 overlying an oxide layer 280 on a silicon semiconductor substrate 290;
- etching first trench 275 into said silicon layer 265 wherein said first trench 275 extends partially through said silicon layer 265 and does not extend to underlying said oxide layer 280 and wherein no implant is made underlying said first trench 275;
- filling said first trench 275 with insulating layer such as oxide (paragraph [0022]);
- etching second trenches 270 into said silicon layer 265 wherein said second trenches 270 extend fully through said silicon layer 265 to underlying said oxide layer 280 and wherein said second trenches 270 separate active areas 220, 250, 260 of said semiconductor substrate and wherein one said first trenches 275 lies within each of said second said active areas 210;
- filling said second trenches 270 with an insulating layer (paragraph [0022]);
- thereafter forming gate electrodes 200 or 520 and associated and drain regions
 210/220 or 490/500 and on said silicon layer 265 between said second trenches 270;
 and
- depositing a dielectric layer 530 overlying said gate electrodes 230 and 240 (Fig.6B).
 In contrast, Babcock et al., neither teach nor suggest depositing an interlevel dielectric

layer overlying said gate electrodes; opening first contact openings through said interlevel

Art Unit: 2823

dielectric layer to underlying said source and drain regions and opening a second contact opening through said interlevel dielectric layer, wherein said second contact opening contacts both said first trench and one of said second trenches; and filling first and second contact openings with conducting layer to complete formation silicon-on-insulator device in said fabrication integrated circuits.

The primary reason for allowance of the claims is that aforementioned patentably distinct features show unexpected results as compared to the prior art.

- 8. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."
- 9. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Hsien-Ming Lee whose telephone number is 571-272-1863. The examiner can normally be reached on M-F (9:00 \sim 5:00).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Olik Chaudhuri can be reached on 571-272-1855.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Art Unit: 2823

Hsien-Ming Lee Examiner Art Unit-2823

April 13, 2004

Kend Mig Len 4/B/04 Page 5